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(54) SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

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(57)ABSTRACT

A reliability of a semiconductor device is ensured, and performance of the device is improved. A semiconductor device including a region 1A and a region 2A includes an n-type semiconductor substrate TS having a front surface BS1, BS2 and a back surface SUB, a IGBT formed on a semiconductor substrate in a region 1A, and a diode formed on the semiconductor substrate SUB in a region 2A. And a thickness T1 of the semiconductor substrate SUB in the region 1A is smaller than a thickness of the semiconductor substrate T2 in the region 2A.

A-A cross section

